

PATENT ABSTRACTS OF JAPAN

(11)Publication number : 2002-003284

(43)Date of publication of application : 09.01.2002

(51)Int.Cl.

C04B 41/87
B23B 27/14
B23P 15/28
C04B 41/89
C23C 14/06

(21)Application number : 2000-178137

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(22)Date of filing : 14.06.2000

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(54) HARD COATING ULTRAHIGH TEMPERATURE HIGH PRESSURE SINTERED MATERIAL**(57)Abstract:**

PROBLEM TO BE SOLVED: To provide a hard coating sintered material used for cutting tools, etc., with improved adhesion of hard coating and adjacent material.

SOLUTION: This is the hard coating ultrahigh temperature high pressure sintered material consisting of coated base material of ultrahigh temperature high pressure sintered material containing cubic system boron nitride and/or diamond and its coating containing hard coating of one kind of single layer or multi layers of more than two kinds chosen among Ti compounds layers and Ti-Al compounds layers and its coating consisting of cubic system crystal structure. Regarding the hard coating, when an X-ray diffraction is carried out on the indicated range of crystal faces (111), (200), (220), and (311) of the hard coating, (200) crystal face shall show the highest peak strength (shown as 'A') of X-ray diffraction peaks and shall have the relation of $A/B \geq 8.5$ against the second highest peak strength (shown as 'B') and the relation of $B/C \leq 2.0$ between B and the third highest peak (shown as 'C').

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DETAILED DESCRIPTION

[Detailed Description of the Invention]

[0001]

[Field of the Invention]This invention relates to the rigid film covering super-high-temperature-high-pressure sintered compact with which the tunic containing the rigid film which comes by the monolayer of a Ti compound layer and/or a Ti-aluminum content compound layer or a multilayer on the substrate of the super-high-temperature-high-pressure sintered compact containing cubic boron nitride and/or a diamond was covered.

[0002]

[Description of the Prior Art]The super-high-temperature-high-pressure sintered compact which sintered from the former powder mixture with the diamond which is a super-high hardness substance, the powder of cubic boron nitride and metal, and/or the powder of ceramics with a super-high-temperature-high-pressure device is used. This super-high-temperature-high-pressure sintered compact is used as a substrate, and the rigid film covering sintered compact which covered the rigid film on this substrate using chemical vapor deposition (henceforth a "CVD method"), physical vapor deposition (henceforth "PVD"), or plasma CVD method is proposed. JP,59-8679,A, JP,61-183187,A, JP,1-96083,A, JP,1-96084,A, and JP,7-24606,A are one of the typical things of this rigid film covering sintered compact.

[0003]Cemented carbide, the sintered alloy of a cermet, or a ceramic sintered body is used as a substrate from the former, and it has used with gestalten with a various covering sintered member which covered the rigid film on this substrate using a CVD method, PVD, or plasma CVD method. Although the crystal structure of the rigid film was observed among these covering sintered members, to a typical thing. JP,52-28478,A, JP,8-209335,A, the publication-number No. 291353 gazette, JP,9-295204,A, JP,9-300105,A, JP,9-300106,A, JP,9-323204,A, JP,9-323205,A, JP,10-76407,A, There are JP,10-76408,A, JP,11-1762,A, JP,11-131214,A, JP,11-131215,A, JP,11-131216,A, and JP,11-131217,A.

[0004]

[Problem(s) to be Solved by the Invention]JP,59-8679,A among the cited documents quoted as conventional technology, To JP,61-183187,A, JP,1-96083,A, JP,1-96084,A, and JP,7-24606,A. The super-high-temperature-high-pressure sintered compact which mainly contained cubic boron nitride is used as a substrate, and the rigid film covering sintered compact which covered rigid films, such as carbide of Ti, a nitride, carbon nitride, and an aluminum oxide, to this base material surface at the monolayer or the multilayer is indicated. The rigid film covering sintered compact of an indication in the gazette of these five affairs may be characterized [main] by the substrate composition component of a sintered compact, when characterized [main] by the composition of the rigid film which becomes by the monolayer or a multilayer when characterized [main] by the membraneous quality of a rigid film. Although it is thought that the rigid film covering sintered compact of an indication is uniting with the gazette of these five affairs apparently the effect which was excellent in the substrate itself, and the effect which was excellent in the rigid film itself, since it is not considered in particular about the conformity of a substrate and a rigid film, there is a problem of becoming a short life by exfoliation of a rigid film. It stems from an ecology problem like recent years, and a saving-resources problem, As opposed to a cutting tool suitable for a demand of commercial scenes, such as the optimal cutting tool accompanying diversification including the material change etc. of the tool for dry cutting and work material which are cut without using cutting oil, further high speed cutting condition, a heavy load cutting condition, and a highly efficient cutting condition, etc., There is a problem that the rigid film covering sintered body of an indication in the 5 affair gazette has a high tendency which becomes a short life with shortage of the ease of exfoliating of a rigid film or heat resistance, and thermal shock resistance etc.

[0005]JP,52-28478,A, JP,8-209335,A quoted as other cited documents, The publication-number No. 291353 gazette, JP,9-295204,A, JP,9-300105,A, JP,9-300106,A, JP,9-323204,A, JP,9-323205,A, JP,10-76407,A, JP,10-76408,A, JP,11-1762,A, To JP,11-131214,A, JP,11-131215,A, JP,11-131216,A, and JP,11-131217,A. Cemented carbide, the sintered alloy of a cermet, or a ceramic sintered body is used as a substrate, The covering sintered member with which the rigid film of the Ti-aluminum content compound which comes on this substrate by the complex nitrides, the complex carbide, compound carbonitride, the compound nitric oxide, compound carbonation thing, and compound charcoal nitric oxide containing periodic table 4a fellows' carbide, nitride, carbon nitride and titanium, and aluminum was covered is indicated.

[0006]The covering sintered member of the indication in the gazette of these 15 affairs carried out orientation of the rigid film of a base material surface mainly to various gestalten. When the residual compressive stress in a rigid film is being taken into consideration in the gazette of these 15 affairs, or the crystal orientation in a rigid film may be taken into consideration, and control of the intergranular fracture in a rigid film, improvement in the adhesion of a substrate

and a rigid film, wear-resistant improvement, stable cutting, or long lasting achievement is indicated as the effect. However, the covering sintered member of an indication in the gazette of these 15 affairs, From the defect of a crystal and distortion which exist in a rigid film not being considered, and not being considered in particular about the conformity of a substrate and a rigid film. Cannot be satisfied with adhesion with other films which adjoin the adhesion and the rigid film of a substrate and a rigid film, By the time it also satisfies the intensity of the rigid film itself, and abrasion resistance, it will not result, but the variation in a life is large and there is a problem of mainly becoming a short life with the shortage of the ease of exfoliation of a rigid film or heat resistance, thermal shock resistance, etc., to a demand of a commercial scene which was mentioned above when it used as a cutting tool.

[0007] This invention is the above problems what was solved, and specifically, By mainly considering the crystal structure conformity of the substrate of a super-high-temperature-high-pressure sintered compact, and the rigid film which adjoins this substrate and is covered, the defect of the crystal of a rigid film, distortion, a crystal structure, and crystal orientation, Improve the adhesion of a substrate and a rigid film extremely and the variation in the characteristic of a rigid film is controlled, It is considered as a rigid film with high toughness, high hardness nature, abrasion resistance, oxidation resistance, thermal shock resistance, defect resistance, and welding-proof nature, The usage region as a cutting tool is expanded and it aims at offer of the rigid film covering super-high-temperature-high-pressure sintered compact which made a long life attain further by considering it as the rigid film which raised welding-proof nature with a work material.

[0008]

[Means for Solving the Problem] Research on membrane formation of a rigid film concerning [this invention person] a CVD method, PVD, and plasma PVD, A result which continued at a long period of time and has done research on a rigid film especially by PVD, When making the surface of a substrate which becomes with a super-high-temperature-high-pressure sintered compact containing cubic boron nitride and/or a diamond cover a rigid film which becomes by Ti compound layer and/or a Ti-aluminum content compound layer, knowledge that there is optimal rigid film composition is acquired. If it changes into the state of performing improvement in plasma density at the time of membrane formation of a rigid film, and improvement in ionization efficiency, and making it gaseous-phase-method-growing epitaxially further when this knowledge is explained concretely, A defect of a crystal of a rigid film is controlled [that distortion in a rigid film is eased uniformly,], From that a rigid film of a fine crystal is obtained, and becoming a rigid film of a crystal which is not seen and which changed orientation into optimal state extremely at the former. The 1st knowledge that become possible to raise intensity, abrasion resistance, oxidation resistance, and heat resistance of the rigid film itself, and improvement in the adhesion of a rigid film and a substrate becomes remarkable,

When the X diffraction of the oriented state of a crystal of a rigid film is carried out from the surface of a rigid film, its 2nd knowledge that it can judge when peak intensity of a crystal face becomes extremely high to other crystal faces (200) in a rigid film is main. Based on these knowledge, it comes to complete this invention.

[0009] A tunic is covered by the surface of a substrate which becomes with a super-high-temperature-high-pressure sintered compact containing cubic boron nitride and/or a diamond, and a rigid film covering super-high-temperature-high-pressure sintered compact of this invention this tunic, A Ti compound layer which becomes by carbide of titanium, a nitride, carbon nitride, a carbonation thing, nitric oxide, and a charcoal nitric oxide, And complex nitrides, complex carbide, compound carbonitride containing titanium and aluminum, It has one sort of monolayers or two or more sorts of multilayer rigid films selected from Ti-aluminum content compound layers which become by compound nitric oxide, compound carbonation thing, and a compound charcoal nitric oxide, This rigid film that adjoins this substrate and is covered consists of a cubic crystal structure, and a copper target is used from the surface of this rigid film, When the X diffraction of the range as which a crystal face of (111) of this rigid film, (200), (220), and (311) is displayed is carried out, a crystal face (200) shows high peak intensity (it expresses "A") to the 1st in an X diffraction peak, and high peak intensity (it expresses "B") is received the 2nd -- this -- a ratio of high peak intensity becoming the 1st or more from 8.5 ($A/B \geq 8.5$), and to it, and peak intensity (it expresses "C") high to the 3rd is received -- this -- a ratio of high peak intensity (B) becomes the 2nd or less by 2.0 ($B/C \leq 2.0$)

[0010] A rigid film covering super-high-temperature-high-pressure sintered compact of this invention applies gaseous phase method epitaxial growth technology, Intensity of the rigid film itself and toughness are improved by strengthening orientation of a crystal face in a rigid film (200) which becomes by monolayer of a Ti compound layer and a Ti-aluminum content compound layer, or a multilayer, and controlling distortion in a rigid film as much as possible, and the SHINAJI effect that abrasion resistance is also excellent is demonstrated. When an X diffraction is carried out using a copper target from the surface of this rigid film, peak intensity (A) of a crystal face over high peak intensity (B) (200) to the 2nd by less than 8.5 ($A/B < 8.5$), and peak intensity (C) high to the 3rd is received -- this, when a ratio of high peak intensity (B) becomes high the 2nd exceeding 2.0 ($B/C > 2.0$), (200) Since a stacking tendency to a crystal face is weak, a defect in a film and distortion become large and the above-mentioned SHINAJI effect becomes weak, determine it as a peak height ratio of the above crystal faces. In consisting of $A/B \geq 9.0$ and $B/C \leq 1.5$ is preferred as for a peak intensity ratio of this crystal face and becoming by $A/B \geq 10.0$ and $B/C \leq 1.5$ especially, The much more crystal orientation promotion and control of a defect or distortion will be caused, adhesion with a substrate will be improved, and it is desirable.

[0011]

[A mode of implementation of an invention] Using a super-high-temperature-high-pressure sintered compact containing cubic boron nitride and/or a diamond which serve as practical use or common knowledge from the former cuts a substrate in a rigid film covering super-high-temperature-high-pressure sintered compact of this invention. With a substrate of a super-high-temperature-high-pressure sintered compact which cubic boron nitride contained, for example, specifically, 20 to 98 % of the weight and the remainder content of cubic boron nitride 4a and 5a of the periodic table, 6a fellows' metal, Mn, Fe, nickel, Co, Si, aluminum, metal of Mg, A cubic boron nitride C containing sintered body which becomes these alloys, these carbide, a nitride, an oxide, boride, and one or more sorts of qualitatively [selected from these mutual solid solutions] of a reinforcement dispersed matter can be mentioned. In a substrate of a super-high-temperature-high-pressure sintered compact which a diamond contained, for example, a diamond C containing sintered body which becomes about content of a diamond 70 to 99 % of the weight and qualitatively [with the above-mentioned remainder] of a reinforcement dispersed matter can be mentioned. In a substrate of a super-high-temperature-high-pressure sintered compact in which cubic boron nitride and a diamond were intermingled, for example, a sintered compact which will be 15 to 80 % of the weight about content of a diamond in content of cubic boron nitride 15 to 80 % of the weight and qualitatively [with the above-mentioned remainder] of a reinforcement dispersed matter can be mentioned.

[0012]Cubic boron nitride among these substrates 40 to 98 % of the weight, Compound boride in which the remainder contains carbide of Ti, a nitride, carbon nitride and boride, a nitride of aluminum, an oxide, boride and a nitride of Si, carbide, an oxide of Mg, carbide of W and these mutual solid solutions, Ti, and aluminum and Mg, compound ***** and aluminum, Ti, Co, nickel, Si, In becoming with these mutual alloys and a super-high-temperature-high-pressure sintered compact containing at least one sort of quality of a reinforcement dispersed matter selected from intermetallic compounds, Orientation of a rigid film covered by base material surface comes to be [excelling in the characteristics, such as intensity of the substrate itself, and high hardness] easily excellent, That is, it is desirable from an X diffraction peak of a crystal face (200) becoming extremely high to other crystal faces among crystal faces of (111), (200), (220), and (311), and excelling in the adhesion of a substrate and a rigid film, and a defect in a rigid film being controlled.

[0013]These substrates are desirable things from frictional resistance becoming low, roughness on the rigid film surface and the surface of a work material being controlled, and a life improved effect becoming high, when surface accuracy was made high, and a tendency for surface accuracy of a rigid film covered by base material surface to also become high is shown, for example, is used as a cutting tool. As for surface accuracy of a substrate, 0.1 micrometer or less is preferred at Ra which is the arithmetical mean deviation of profile in surface roughness specified to JIS B0601, and, as for more desirable one, Ra consists of 0.05

micrometer or less.

[0014]If composition of a tunic covered by these base material surfaces is concretely divided roughly, when a base material surface will be adjoined and only a rigid film will be covered directly, a rigid film and other films other than a rigid film may be covered by base material surface. Among these, if the latter tunic composition is explained, composition with which a film besides substrate-rigid film - was covered one by one, composition with which a film-rigid film besides substrate-rigid film - was covered one by one, and composition by which a rigid film and other films were laminated twice or more repeatedly, respectively can be mentioned. A rigid film which adjoins a substrate and is covered consists of a cubic crystal structure among these, and crystal orientation by an X diffraction mentioned above is performed.

[0015]When the surface of a rigid film which these tunic surfaces adjoin a substrate and is covered turns into the tunic surface as it is, other films may serve as the tunic surface. By arithmetical-mean-deviation-of-profile Ra in surface roughness specified to JIS B0601, 0.1 micrometer or less, if this tunic surface shall be 0.05 micrometer or less preferably, When it is used as a cutting tool, it is much more desirable thing that becomes long lasting from that damage to a work material is eased, that cutting force is eased, and discharge of a chip becoming easy.

[0016]As this tunic composition, about fundamental composition of a rigid film, if it explains in detail still more concretely, A substrate-TiN layer, a substrate-TiC layer, a substrate-Ti (N, C) layer, a substrate-Ti (N, O) layer, A substrate-Ti (C, O) layer, a substrate-Ti (N, C, O) layer, a substrate-(Ti, aluminum) N layer, A substrate-(Ti, aluminum) (N, C) layer, a substrate-(Ti, aluminum) (N, O) layer, A substrate-TiN layer-(Ti, aluminum) N layer, a substrate-Ti (N, C) layer-(Ti, aluminum) N layer, A substrate-Ti (N, O) layer-(Ti, aluminum) N layer, a substrate-Ti (C, O) layer-(Ti, aluminum) N layer, a substrate-Ti (N, C, O) layer-(Ti, aluminum) N layer, or a rigid film that laminated three or more layers of these can be mentioned as an example of representation.

[0017]As tunic composition adapting these rigid films, A substrate-TiN layer-aluminum₂O₃ layer and substrate-Ti (N, O) layer-aluminum₂O₃ layer, A substrate-(Ti, aluminum) N layer-aluminum₂O₃ layer and substrate-(Ti, aluminum) (N, O) layer-aluminum₂O₃ layer, A substrate-TiN layer-(Ti, aluminum) N layer-aluminum₂O₃ layer and substrate-TiN layer-(Ti, aluminum) (N, O) layer-aluminum₂O₃ layer, A substrate-TiN layer-columnar crystal Ti (C, N) layer-aluminum₂O₃ layer, A substrate-Ti (N, O) layer-columnar crystal Ti (C, N) layer-aluminum₂O₃ layer, A substrate-TiN layer-aluminum₂O₃ layer-TiN layer, a substrate-Ti (N, O) layer-aluminum₂O₃ layer-TiN layer, A substrate-(Ti, aluminum) N layer-aluminum₂O₃ layer-TiN layer

and substrate-(Ti, aluminum) (N, O) layer-aluminum₂O₃ layer-TiN layer, A substrate-TiN layer-(Ti, aluminum) N layer-aluminum₂O₃ layer-TiN layer, a substrate-TiN layer-(Ti, aluminum) (N, O) layer-aluminum₂O₃ layer-TiN layer, substrate-TiN layer - Columnar crystal Ti (C, N) layer-aluminum₂O₃ layer-TiN layer, Or substrate-Ti (N, O) layer - A columnar crystal Ti (C, N) layer-aluminum₂O₃ layer-TiN layer can be mentioned as an example of representation.

[0018]In becoming with a monolayer or a multilayer rigid film which adjoins a substrate among these tunic composition and is covered, It excels in adhesion by being the same crystal structure as cubic boron nitride and/or a diamond which a rigid film contains in a substrate, It is desirable from cubic boron nitride in that a coating process of a tunic is simple, becoming shortening of process time, that variation on a quality control decreases, and a substrate at the time of rigid film covering and/or an inverse transformation preventive effect of a diamond being easy. If it has tunic composition which becomes in a layer of a rigid film contiguous to a substrate, and an aluminum oxide contiguous to this rigid film, or tunic composition which repeated and laminated a layer of a rigid film and an aluminum oxide, it is desirable from demonstrating synergistically an effect by a layer of an aluminum oxide of improving heat resistance in a high temperature region, oxidation resistance, and abrasion resistance further with an effect of a rigid film which adjoins a substrate mentioned above and is covered.

[0019]A rigid film contiguous to a substrate which becomes indispensable constituting these tunics has a case of a Ti compound layer which becomes by monolayer or a multilayer. this Ti compound layer -- $\text{Ti}(\text{C}_x, \text{N}_y, \text{O}_z)_w$ -- however, An atomic ratio of carbon (C) element in a nonmetallic element and $y \times$ An atomic ratio of nitrogen (N) element in a nonmetallic element, An atomic ratio of a nonmetallic element to titanium (Ti) element whose z is an atomic ratio of oxygen (O) element in a nonmetallic element and whose w is a metallic element is expressed, When each becomes by a Ti compound layer expressed with $x+y+z=1$, $0.5 \geq x \geq 0$, $1 \geq y \geq 0.5$, $0.5 \geq z \geq 0$, and] that has a relation of $1.05 \geq w \geq 0.7$, it is desirable from demonstrating an effect of an above-mentioned rigid film easily.

[0020]A rigid film contiguous to a substrate has a case of a Ti-aluminum content compound layer which becomes by monolayer or a multilayer. this Ti-aluminum content compound layer -- $(\text{C}(\text{Ti}_a, \text{aluminum}_b)_x, \text{N}_y, \text{O}_z)_w$ -- however, An atomic ratio of Ti (titanium) element in a metallic element and $b \times$ An atomic ratio of aluminum (aluminum) element in a metallic element, An atomic ratio of carbon (C) element in a nonmetallic element and $y \times$ An atomic ratio of nitrogen (N) element in a nonmetallic element, An atomic ratio [as opposed to / as opposed to / in z / an atomic ratio of oxygen (O) element in a nonmetallic element / the sum total of a metallic element in w] of a nonmetallic element is expressed, each -- $a+b$ -- -- one -- $0.8 \geq a$ -- \geq -- zero . -- four -- $x+y+z$ -- -- one -- $0.5 \geq x$ -- \geq -- zero -- one -- \geq -- y -- \geq -- zero .

-- five -- 0.5 -- >= -- z -- >= -- zero -- 1.05 -- >= -- w -- >= -- 0.7 -- a relation -- it is --] --
 expressing -- having -- Ti-aluminum -- content -- a compound layer -- becoming -- a case --
 ****. It is desirable from excelling in abrasion resistance excelling in adhesion and compatibility
 in a field side of a substrate, a rigid film, and an aluminum oxide with a layer, and hot, and
 oxidation resistance. A rigid film may consist of a multilayer which becomes by Ti compound
 layer and a Ti-aluminum content compound layer, and composition of this rigid film is desirable
 from demonstrating abrasion resistance and oxidation resistance in a larger temperature range
 with the same effect as ****.

[0021]When a Ti-aluminum content compound layer exists in all the rigid films including a rigid
 film contiguous to these substrates, aluminum elemental content in a Ti-aluminum content
 compound layer is decreasing toward the substrate side from the surface side of a Ti-
 aluminum content compound layer, It is desirable from excelling in intensity of that the
 adhesion of a substrate and a rigid film is excellent, and the rigid film itself, and toughness, if
 the so-called rigid film of an inclination presentation is used, and oxidation resistance on that a
 defect, distortion, and remaining stress decrease and the surface of a rigid film, abrasion
 resistance, and corrosion resistance being excellent. Though reduction of aluminum element at
 this time has increase and decrease in stair-like and edge shape of a saw in micro, when it
 decreases gradually on a macro target, a case where it is decreasing continuously to parabolic
 and linear shape may be sufficient as it.

[0022]A rigid film which becomes by these Ti compound layers and/or a Ti-aluminum content
 compound layer, especially a rigid film contiguous to a substrate, the inside of this rigid film --
 4a and 5a of the periodic table, 6a group metal, iron-group metal, aluminum, Si, Mn, and Mg --
 a little alloys of these or at least one sort of rigid film strengthening substances in an
 intermetallic compound may contain. In becoming by at least one sort chosen among these
 rigid film strengthening substances from metal of nickel, Co, W, Mo, aluminum, and Ti, these
 mutual alloys, and these intermetallic compounds, It is desirable from a defect and distortion
 being eased, and an effect of the above-mentioned rigid film improving further, and becoming
 remarkable. Especially in the case of an element contained in a substrate, and a substrate
 which becomes by the above-mentioned cubic boron nitride C containing sintered body
 concrete, for example, when it consists of an element which constitutes quality of a
 reinforcement dispersed matter, it is a desirable thing from improving one layer of effect nearby
 of the adhesion of a substrate and a rigid film with an effect of the above-mentioned rigid film.

[0023]As content of these rigid film strengthening substances, specifically, When below 1
 volume % contains [below 3 volume %] preferably to the sum total of a rigid film and a rigid
 film strengthening substance, while excelling in compression strength-proof of the from both [a
 perpendicular direction and / horizontal] the surface, and compressive strength-proof, [of a
 composite hard film] [both] From a synergistic effect of excelling also in abrasion resistance

being demonstrated, it is desirable.

[0024]When a columnar crystal which grew perpendicularly pillar-shaped to a base material surface as a structure of the rigid film itself is contained, it is desirable from compression strength-proof from the surface of a composite hard film improving, and excelling in peeling resistance and minute-proof chipping nature. When, as for a rigid film containing this columnar crystal, the whole rigid film specifically becomes in a layer of a columnar crystal, When becoming in an intermingled layer of a granular crystal and a columnar crystal and becoming in lamination with a layer of a granular crystal, and a layer of a columnar crystal, a case where a little rigid film strengthening substances mentioned above in each of these granular crystals and columnar crystals contain can be illustrated.

[0025]A rigid film covering super-high-temperature-high-pressure sintered body of this invention which becomes in various kinds of above modes, It can use for various kinds of uses, and, specifically, can use as tools for abrasion proof, such as the cutting edge, such as a slitting machine, and a decision edge, for example from die tools, such as a lathe-turning tool, a milling cutter tool, a drill, a cutting tool represented by end mill, and a dice. Among these a rigid film covering super-high-temperature-high-pressure sintered body of this invention, When temperature, friction, a thermal shock, a compression shock, etc. use it in micro as cutting tools, such as rotary cutting tools, such as a cutting tool which serves as a severe condition most especially a drill, and an end mill, and a throwaway tip, it is desirable from demonstrating the characteristic of a substrate and a rigid film the optimal. In using this rigid film covering super-high-temperature-high-pressure sintered body as a cutting tool, there is a problem of a cutting edge relevant to a nick, chipping, etc. besides a problem of profile irregularity in the surface mentioned above. A problem of this cutting edge is desirable [it is also preferred to solve, for example with honing shape, such as camfering and/or R form, and] from excelling in the peeling resistance of a tunic, and the minute chipping nature of a cutting edge, when coating thickness is decreasing toward a cutting blade ridgeline part especially.

[0026]Film thickness of each class which constitutes a tunic is that it is preferred that the total film thickness of a tunic shall be 1-20 micrometers, when choosing is preferred and it uses it for the severest cutting tool etc. by composition of a use, shape, and a tunic. When using it for a wear-proof tool etc., it is also possible to thicken film thickness of a tunic further, but it is that it is preferred to use the above-mentioned total film thickness grade from a coating process serving as a long time etc. When becoming with stoichiometric composition, a case where it becomes with non-stoichiometric composition may be sufficient as quality of a reinforcement dispersed matter which first contains in a substrate a rigid film explained in full detail above, and it consists of non-stoichiometric composition substantially in many cases.

[0027]A rigid film covering super-high-temperature-high-pressure sintered body of this invention, A super-high-temperature-high-pressure sintered compact or a super-high-

temperature-high-pressure sintered compact of cubic boron nitride content mentioned above represented by a cubic boron nitride system sintered compact marketed from the former and diamond system sintered compact is used as a substrate, After grinding the surface of this substrate if needed and performing ultrasonic cleaning, organic solvent cleaning, etc., a tunic can be covered with PVD, a CVD method, or plasma CVD method currently performed from the former on a substrate, and it can produce. Especially a rigid film that adjoins a base material surface and is covered, When it produces by the following PVD, the characteristic and adhesion of that gaseous phase epitaxial crystal growth and crystal orientation of that improvement in plasma density and improvement in ionization efficiency are attained and the rigid film itself become easy and a rigid film are a desirable thing from excelling more.

[0028]When the important feature is concretely explained in full detail as a method for covering a rigid film which adjoins a base material surface and is covered, the surface of a substrate, At least one sort of mechanical processes in blast processing, a shot peening process, grinding treatment, and barrel processing which are performed from the former, At least one sort of chemical preparation in washing by surface corrosion by electrolytic etching by an acid or alkaline electrolysis solution, an acid solution, and an alkali solution or water, and an organic solution, When processing chosen from a disposal method which performs this mechanical process and chemical preparation simultaneous or independently is performed, it is desirable from the ability to control [that a defect of a base material surface is removable, that the adhesion of a rigid film can be improved that distortion in a film can be controlled, and] a defect in a film. A substrate is that it is also preferred to add such mechanical treatment and/or chemical preparation, and heat treatment by low temperature, and to heighten an above-mentioned effect.

[0029]If it is preferred to carry out by PVD represented by a sputtering technique and the ion plating method as for a coating method of a rigid film and it carries out by the magnetron sputtering method or the arc-plasma ion plating method among these, From adjustment of a rigid film being easy, it is especially desirable. A substrate is specifically arranged, for example in a reaction vessel of an ion plating system, When carrying out bombardment processing of the base material surface and bombardment processing by ion of a metallic element and/or a nitrogen element or bombardment processing by both metallic element ion and nonmetallic element ion is performed, an above-mentioned effect will be heightened and it is desirable.

[0030]The coating method of a still more concrete rigid film needs to attach importance to influence of the device itself, such as adjustment of structure of a reaction vessel, and plasma, For example, a thing for which a device made to generate acceleration and plasma of ion with a power supply (pulse form high tension and high frequency are added depending on the case) of high tension and a device which can adjust plasma by a magnetic field are used, In addition, a thing for which it is necessary to consider about arrangement of ambient pressure power in a

reaction vessel, temperature, arc-discharge-currents . voltage, substrate bias voltage, and a sample, etc., and especially arc discharge voltage is made high to the conventional conditions among these, Rotation, up-and-down motion, etc. of making substrate bias voltage high, taking in a gaseous phase epitaxial crystal growth method currently performed from the former, and a sample serve as important requirements.

[0031]

[Embodiment of the Invention]

[Operation examination 1] An operation examination explains the embodiment of this invention explained in full detail above as a still more concrete example of representation. First, the cemented carbide of SNGN120408 shape by the ISO standard produced through each process of the conventional combination, mixing, shaping, and sintering is made into base metal, The substrate of the super-high-temperature-high-pressure sintered compact of the cubic boron nitride content which becomes a corner part used as the edge of a blade of this cemented carbide base metal by the composition component shown in Table 1 was joined, and the compound sintered compact was obtained. This compound sintered compact joins directly the cubic boron nitride content composition component shown in cemented carbide base metal and Table 1 by pressure 5.5GPa and super-high-temperature-high-pressure sintering of the temperature 1773K. The case where a super-high-temperature-high-pressure sintered compact is joined to cemented carbide base metal by silver low attachment may be sufficient as a compound sintered compact. A grinding process is performed for the upper and lower sides and the peripheral face of these compound sintered compacts by the diamond wheel of 270#, The rigid film was covered with the arc ion plating system, after performing -25 degreeex0.10mm honing to the tip part by the 400# diamond wheel and performing wet blast processing, washing processing, and a drying process for the surface further.

[0032]The disposal method covered the rigid film, after carrying out bombardment processing of each compound-sintered-compact surface (especially base material surface) in a reaction vessel. Bombardment processing set [the temperature of the vacuum and the substrate] bias voltage of 60-80A, and a substrate to -400 - -700V for 823-873K, and an arc current, and performed atmosphere in a reaction vessel by Ar-N₂ gas bombardment. Covering of a rigid film 150 - 450SCCM and an evaporation source for the gas mass flow in a reaction vessel Ti metal (for Ti compound layers), or Ti-aluminum alloy (for Ti-aluminum content compound layers), this invention article 1-10 which performed [150-350V, and an arc current] 773-923K, and substrate bias voltage of the compound sintered compact for 150-250A, and the substrate temperature of the compound sintered compact by -100 - -200V, and showed arc voltage in Table 2 was obtained.

[0033]The atmosphere in a reaction vessel at the time of rigid film covering at this time, The case where the cases of a TiN layer and (Ti, aluminum) N layer are N₂ gas composition and Ti

(C, N) layer N_2 - C_2H_4 gas composition, The case where the cases of a TiC layer are CH_4 gas composition and Ti (N, O) layer N_2 -CO-CO₂ gas composition, It carried out by the N_2 - CH_4 -CO gas presentation, and carried out by the case of Ti (C, N, O) layer having changed from the alloy with many Ti elements to the evaporation source of this invention article 4 to the alloy with many aluminum elements, and this invention article 1-10 with which the rigid film shown in Table 2 was covered was obtained.

[0034]The rigid film shown in Table 3, respectively was covered on the surface of the isomorphism-like compound sintered compact which obtained it as comparison by carrying out silver low attachment of the super-high-temperature-high-pressure sintered compact of the cubic boron nitride content marketed at cemented carbide, and the comparison article 1-5 was obtained. The surface of the compound sintered compact of use in the above-mentioned this invention article 1-10 was [the surface of the compound sintered compact of use in the comparison article 1-5 of the surface roughness of the compound sintered compact] $Ra=0.1$ - 0.05 micrometer to $Ra=0.01$ - 0.005 micrometer. Except for wet blast processing, others were processed almost in a similar manner among the surface treatments of this invention article which the surface treatment of the compound sintered compact in the comparison article 1-5 mentioned above. Ar gas performed bombardment processing in the comparison article 1-5, and covering of the rigid film processed arc voltage almost in a similar manner among the processing conditions of the rigid film of this invention article mentioned above except having set 150-200A, and substrate bias voltage to -80 ~ $-200V$ for 10-50V, and an arc current.

[0035]In this way, about each of the obtained this invention article 1-10 and the comparison article 1-5 with X-ray diffractometer. Using Cu target, the range of angle-of-diffraction degree $2\theta=30$ -80 degree was diffracted from the rigid film surface, and each peak intensity of the crystal face (111) of a rigid film, the crystal face (200), the crystal face (220), and the crystal face (311) was measured. The horizontal axis measured the height of the peak with respectively high intensity to the 1st - the 3rd per mm among the X diffraction patterns as which a vertical axis expresses peak intensity with the degree of angle of diffraction (2θ), and, as for measurement of peak intensity, showed the result in Tables 4 and 5. Although great difference [the peak high to the 1st in this invention article 1-10 of Table 4 was a crystal face (200) and / the 2nd peak high to the 3rd / a crystal face (111), a crystal face (220), and a crystal face (311)] hardly, the crystal face (111) and (311) the crystal face were measured. The comparison article 1-5 of Table 5 measured the crystal face, the crystal face (111), and (311) the crystal face similarly (200). It checked that the rigid film of this invention article 1-10 at this time consisted of a cubic crystal structure.

[0036]About such this invention article 1-10 and the comparison article 1-5, the state of the rigid film was mainly investigated using a scanning electron microscope, the metallurgical microscope, the EDS device, the Vickers hardness tester, and the scratch testing machine that

scratches and is equivalent to a hardness tester. The film thickness of the rigid film was shown in Tables 2 and 3 among these results of an investigation. The scratch intensity measured as peeling resistance of a rigid film showed each result in Table 6. The oxygen content in the rigid film layer of the rigid film which oxygen contained among the rigid films of this invention article 1-10 was 0.2 atomic ratio to the whole nonmetallic element. (Ti, aluminum) The rigid film layer of N was Ti:aluminum=1:1 mostly, among these this invention article 4 was N (Ti, aluminum) rigid film layer of the inclination presentation which aluminum element increased gradually toward the membrane surface from the substrate side. The rigid film layer of Ti (C, N) in this invention article 5 and 10 consisted of a columnar crystal crystal.

[0037] Subsequently, the dry type continuous cutting examination was done according to the following cutting conditions using this invention article 1-10 and the comparison article 1-5. a cutting condition -- in FCD70 and cutting speed, 500 m/min and delivery carried out, and, in 0.1 mm/rev and slitting, 0.3 mm and tool shape carried [the work material] out more, without SNGN120408. When chipping of a cutting edge and an enveloping layer exfoliated, the result of the cutting examination made the tool life the time of the amount of average flank wear amounting to 0.2 mm, found each machining time at that time, set the sample of the shortest life to 1, and wrote it together to Table 6 as a life ratio to the sample of the shortest life.

[0038]

[Table 1]

試料番号	超高強度正統結体の組成成分 (配合時)	体積%
基材 1	98CBN-1Al-1TiN	
基材 2	95CBN-1Al-2Al ₂ O ₃ -2TiN	
基材 3	90CBN-2Al-2B-2Mg-2Al ₂ O ₃ -2TiN	
基材 4	80CBN-2Al-10Al ₂ O ₃ -5TiN-3Ti(C,N)	
基材 5	70CBN-2Al-2B-2Mg-2Si-2Ti-15Al ₂ O ₃ -5TiN	
基材 6	60CBN-10Al-25Al ₂ O ₃ -5Ti(C,N)	
基材 7	40CBN-10Al-35Al ₂ O ₃ -5Ti(C,N)-10TiN	
基材 8	25CBN-25Al ₂ O ₃ -10WC-18Ti(C,N)-10Al-10Ti-2Co-3Mg	

[0039]

[Table 2]

試料番号	試料番号	被膜の膜厚さ(μm)と材質
本発明品	基材番号	被膜膜
1	基材 1	5TiN
2	基材 2	5(Ti,Al)N
3	基材 3	2Ti(C,N)-4(Ti,Al)N
4	基材 4	2TiN-6(Ti,Al)N
5	基材 5	2TiN-4Ti(C,N)-5(Ti,Al)N-1TiN
6	基材 6	2Ti(C,N)-4Ti(N,O)
7	基材 7	2TiC-4Ti(C,N,O)
8	基材 8	3TiN-5(Ti,Al)N-1TiN
9	基材 3	2TiN-2Ti(C,N,O)-1TiN
10	基材 3	2TiN-2Ti(C,N)-1TiN

[0040]

[Table 3]

試料番号	被膜の膜厚さ(μm)と材質
比較品 1	5TiN
比較品 2	5(Ti,Al)N
比較品 3	2Ti(C,N)-4(Ti,Al)N
比較品 4	2TiN-4Ti(N,O)
比較品 5	2TiN-2Ti(C,N)

[0041]

[Table 4]

試料 番号	被覆膜の各結晶面強度			被覆膜の結晶面強度比		
	第1番目(A)	第2番目(B)	第3番目(C)	A/B	B/C	
本 発 明 品	1	70.0	6.5	6.0	10.8	1.1
	2	68.0	4.0	2.5	13.3	1.1
	3	48.5	4.5	4.0	10.8	1.1
	4	45.5	4.0	3.5	11.4	1.1
	5	75.0	5.0	4.0	15.0	1.5
	6	63.5	7.0	5.0	9.1	1.4
	7	67.0	7.0	5.0	9.6	1.2
	8	46.0	4.0	3.5	11.5	1.1
	9	45.0	3.0	3.0	15.0	1.0
	10	47.5	8.0	2.0	15.8	1.5

[0042]

[Table 5]

試料 番号	被膜の各結晶面強度			被膜の結晶面強度比		
	(200)面(A)	(111)面(B)	(311)面(C)	A/B	B/C	
比較品	1	69.0	21.0	15.0	3.3	1.4
	2	58.0	13.0	2.0	4.5	6.5
	3	80.0	C=8.0	B=29.0	2.8	3.5
	4	32.0	53.0	5.0	0.6	10.6
	5	16.0	65.0	8.0	0.2	10.6

[0043]

[Table 6]

試料番号	スクラッチ荷重(N)	切削試験での寿命比	
本 発 明 品	1	140	2.2
	2	130	3.8
	3	130	4.3
	4	140	3.9
	5	160	4.7
	6	140	2.1
	7	150	2.3
	8	140	5.2
	9	150	2.5
	10	140	2.8
比 較 品	1	80	1.0
	2	60	1.4
	3	50	1.6
	4	60	1.1
	5	50	1.2

[0044]

[Operation examination 2] Using the comparison article 1-5 shown in this invention article 1, 2,

3, 4, and 10 and Table 3 showing in Table 2 of the operation examination 1, further on each rigid film surface as other films, The film of aluminum₂O₃ and TiN was covered with the method from the former, and the comparison article 6-10 shown in this invention article 11-15 and Table 8 showing in Table 7, respectively was obtained. In this way, about this invention article 11-15 and the comparison article 6-10 which were obtained, a rigid film and other films were investigated like the operation examination 1, it asked for the scratch intensity from the tunic surface, and the result was shown in Table 9. About this invention article 11-15 and the comparison article 6-10, the cutting examination was done like the cutting condition of the operation examination 1, and it asked for each life ratio to the comparison article 1, and wrote together to Table 9.

[0045]

[Table 7]

試料番号	被膜の膜厚さ(μm)と材質	
	硬質膜	その他の膜
本発明品 11	基材 1 5TiN	2Al ₂ O ₃ -1TiN
12	基材 2 5(Ti,Al)N	4Al ₂ O ₃ -1TiN
13	基材 3 2Ti(C,N)-4(Ti,Al)N	2Al ₂ O ₃ -1TiN
14	基材 4 2TiN-6(Ti,Al)N	2Al ₂ O ₃ -1TiN
15	基材 5 2TiN-2Ti(C,N)-1TiN	2Al ₂ O ₃ -1TiN

[0046]

[Table 8]

試料番号	被膜の膜厚さ(μm)と材質	
	硬質膜	その他の膜
比較品 6	5TiN	2Al ₂ O ₃ -1TiN
比較品 7	5(Ti,Al)N	2Al ₂ O ₃ -1TiN
比較品 8	2Ti(C,N)-4(Ti,Al)N	2Al ₂ O ₃ -1TiN
比較品 9	2TiN-4Ti(N,O)	2Al ₂ O ₃ -1TiN
比較品 10	2TiN-2Ti(C,N)	2Al ₂ O ₃ -1TiN

[0047]

[Table 9]

試料番号	スクラッチ荷重(N)	切削試験での寿命比
本発明品 11	180	4.6
12	160	6.4
13	170	7.5
14	160	6.7
15	180	5.0
比較品 6	100	1.6
7	110	1.8
8	105	1.9
9	90	1.7
10	110	1.6

[0048]

[Operation examination 3] this invention article 16 - the compound sintered compact for 20 were obtained almost similarly except having used the substrate as the composition

component shown in Table 10 among the compound sintered compacts used for this invention article of the operation examination 1. On the surface of these compound sintered compacts, a rigid film and other films were covered like the operation examinations 1 and 2, and this invention article 16-20 shown in Table 11 was obtained. About such this invention article 16-20, like the operation examination 1, the crystal face peak height ratio by the X diffraction in the rigid film surface was calculated, and the result was shown in Table 12. About this invention article 16-20, almost like the operation examinations 1 and 2, it asked for the scratch intensity from a rigid film or the tunic surface, and the result was shown in Table 13. Next, this invention article 16-20 and the comparison article 1 in the operation examination 1 are used, In aluminum-Si alloy and cutting speed, 300 m/min and delivery performed 0.1 mm/rev, slitting performed 0.2 mm, tool shape did the dry type lathe-turning examination according to the cutting condition of SNGN120408, and the work material asked for each life ratio to the comparison article 1, and wrote together the result to Table 13. this invention article 18 and 19 at this time performs a brush honing process with diamond powder and a brush so that the film thickness of a tunic may decrease toward a ridgeline part. Co and/or nickel of ultralow volume contained in the rigid film of this invention article 16-20.

[0049]

[Table 10]

試料番号	焼結体の組成成分 (配合時) 体積%
基材 9	95DIA-2Co
基材 10	95DIA-2Co-3Ni
基材 11	90CBN-90DIA-2Al-2Co-1Ni-5TiN
基材 12	90CBN-60DIA-2Al-4Co-2Ni-2TiN
基材 13	45CBN-45DIA-2Al-2B-2Co-2Ni-2Mg

[0050]

[Table 11]

本発明品	試料番号	被膜の膜厚さ(μm)と材質	
		硬質膜	その他の膜
1 6	基材 9	5TiN	なし
1 7	基材 10	5(Ti,Al)N	なし
1 8	基材 11	2Ti(C,N)-4(Ti,Al)N	なし
1 9	基材 12	2TiN-1Ti(N,O)	3Al ₂ O ₃ -1TiN
2 0	基材 13	2TiN-4Ti(C,N)-1Ti(N,O)	3Al ₂ O ₃ -1TiN

[0051]

[Table 12]

試料番号	硬質膜の各結晶面強度			硬質膜の結晶面強度比	
	第 1 番目(A)	第 2 番目(B)	第 3 番目(C)	A/B	B/C
本発明品 16	68.0	4.0	3.5	17.0	1.1
17	55.0	3.0	3.0	18.3	1.0
18	51.5	3.0	2.5	17.1	1.2
19	65.0	5.5	5.0	11.8	1.1
20	57.0	4.5	4.0	12.7	1.1

[0052]

[Table 13]

試料番号	スクラッチ重量(N)	切削試験での寿命比
本 発 明 品	16	2.0
	17	3.5
	18	5.5
	19	6.0
	20	4.7

[0053]

[Effect of the Invention]The rigid film covering super-high-temperature-high-pressure sintered compact of this invention by consideration by the crystal structure of a substrate and a rigid film, and consideration by a process. The rigid film by the crystal growth and crystal orientation which were approximated to gaseous phase method epitaxial is covered, It is [that distortion by the rigid film itself and a defect are controlled,] a rigid film of a fine crystal, It contrasts with the rigid film covering sintered compact which separated from a conventional rigid film covering sintered compact or this invention from it being the rigid film in which rigid film strengthening substances, such as a columnar crystal crystal and/or a little metal, were contained depending on the case, The adhesion and peeling resistance of a substrate, a rigid film and a rigid film, other films, etc. are dramatically excellent, The high toughness, the high intensity, the heat resistance, the thermal shock resistance, oxidation resistance, and abrasion resistance of the composite hard film itself are excellent, As the result, for example, the thing for which the high toughness, the abrasion resistance, the thermal shock resistance, the defect resistance, oxidation resistance, and welding-proof nature to which importance is attached as a cutting tool improve notably, and reinforcement is attained when it is used as a cutting tool, There is a prominent effect that efficient-ization in cutting being attained and variation are small stable.

[Translation done.]

* NOTICES *

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- 1.This document has been translated by computer. So the translation may not reflect the original precisely.
- 2.*** shows the word which can not be translated.
- 3.In the drawings, any words are not translated.

CLAIMS

[Claim(s)]

[Claim 1]A tunic is covered by the surface of a substrate which becomes with a super-high-temperature-high-pressure sintered compact containing cubic boron nitride and/or a diamond, and this tunic, A Ti compound layer which becomes by carbide of titanium, a nitride, carbon nitride, a carbonation thing, nitric oxide, and a charcoal nitric oxide, And complex nitrides, complex carbide, compound carbonitride containing titanium and aluminum, It has a rigid film which becomes by one sort of monolayers or two or more sorts of multilayers selected from Ti-aluminum content compound layers which become by compound nitric oxide, compound carbonation thing, and a compound charcoal nitric oxide, When the X diffraction of the range as which a crystal face of (111) of this rigid film, (200), (220), and (311) is displayed by this rigid film consisting of a cubic crystal structure using a copper target from the surface of this rigid film is carried out, A crystal face (200) shows high peak intensity (it expresses "A") to the 1st in an X diffraction peak, peak intensity (it expresses "B") high to the 2nd is received -- this - a ratio of high peak intensity becoming the 1st or more from 8.5 ($A/B \geq 8.5$), and to it, and peak intensity (it expresses "C") high to the 3rd is received -- this -- a rigid film covering super-high-temperature-high-pressure sintered compact in which a ratio of high peak intensity (B) becomes the 2nd or less by 2.0 ($B/C \leq 2.0$).

[Claim 2]Compound boride characterized by comprising the following, compound ***** and aluminum, Ti, Co, nickel, Si, these mutual alloys, the rigid film covering super-high-temperature-high-pressure sintered compact containing at least one sort of quality of a reinforcement dispersed matter selected from intermetallic compounds according to claim 1. The above-mentioned substrate is 40 to 98 % of the weight about cubic boron nitride. The remainders are carbide of Ti, a nitride, carbon nitride and boride, a nitride of aluminum, an oxide, boride and a nitride of Si, carbide, an oxide of Mg, carbide of W and these mutual solid solutions, Ti, and aluminum and Mg.

[Claim 3]The rigid film covering super-high-temperature-high-pressure sintered compact according to claim 1 or 2 which consists of 0.1 micrometer or less by average surface roughness according [surface roughness of this substrate] to Ra of JIS in the above-mentioned substrate.

[Claim 4]A rigid film covering super-high-temperature-high-pressure sintered compact given in any 1 paragraph of claims 1-3 which become in lamination characterized by comprising the following.

The above-mentioned tunic is the above-mentioned rigid film.

A layer of an aluminum oxide which adjoined this rigid film and was covered.

[Claim 5]A rigid film covering super-high-temperature-high-pressure sintered compact given in any 1 paragraph of claims 1-4 which consist of 0.1 micrometer or less by average surface roughness according [surface roughness of this tunic] to Ra of JIS in the above-mentioned tunic.

[Claim 6]A rigid film covering super-high-temperature-high-pressure sintered compact given in any 1 paragraph of claims 1-5 for which a columnar crystal the above-mentioned rigid film comes to be perpendicularly pillar-shaped to the surface of the above-mentioned substrate is contained.

[Claim 7]A rigid film covering super-high-temperature-high-pressure sintered compact given in any 1 paragraph of claims 1-6 which the above-mentioned rigid film adjoins the above-mentioned substrate, and are covered.

[Claim 8]The rigid film covering super-high-temperature-high-pressure sintered compact according to claim 7 in which the above-mentioned rigid film which adjoins the above-mentioned substrate and is covered becomes by at least one sort of Ti compound layers in carbide of titanium, a nitride, carbon nitride, a carbonation thing, a nitric oxide, and a charcoal nitric oxide.

[Claim 9]A Ti compound layer to which the above-mentioned Ti compound layer is expressed with $Ti(C_{x'} N_{y'} O_{z'})_w$, An atomic ratio of carbon (C) element in a nonmetallic element and y [, however x An atomic ratio of nitrogen (N) element in a nonmetallic element, An atomic ratio of a nonmetallic element to titanium (Ti) element whose z is an atomic ratio of oxygen (O) element in a nonmetallic element and whose w is a metallic element is expressed, The rigid film covering super-high-temperature-high-pressure sintered compact containing] where each has a relation of $x+y+z=1$, $0.5 \geq x \geq 0$, $1 \geq y \geq 0.5$, $0.5 \geq z \geq 0$, and $1.05 \geq w \geq 0.7$ according to claim 8.

[Claim 10]The rigid film covering super-high-temperature-high-pressure sintered compact according to claim 7 in which the above-mentioned rigid film which adjoins the above-

mentioned substrate and is covered becomes by at least one sort of Ti-aluminum content compound layers in complex nitrides, complex carbide, compound carbonitride, a compound nitric oxide, a compound carbonation thing, and a compound charcoal nitric oxide containing titanium and aluminum.

[Claim 11]Ti-aluminum content compound layer [to which the above-mentioned Ti-aluminum content compound layer is expressed with $(C(Ti_a, aluminum_b)_x \cdot N_y \cdot O_z)_w$ -- however, An atomic

ratio of Ti (titanium) element in a metallic element and b a An atomic ratio of aluminum (aluminum) element in a metallic element, An atomic ratio of carbon (C) element in a nonmetallic element and y x An atomic ratio of nitrogen (N) element in a nonmetallic element, An atomic ratio [as opposed to / as opposed to / in z / an atomic ratio of oxygen (O) element in a nonmetallic element / the sum total of a metallic element in w] of the sum total of a nonmetallic element is expressed, each -- a+b -- = -- one -- 0.8 -- >= -- a -- >= -- zero . -- four -- x+y+z -- = -- one -- 0.5 -- >= -- x -- >= -- zero -- one -- >= -- y -- >= -- zero . -- five -- 0.5 -- >= -- z -- >= -- zero -- 1.05 -- >= -- w -- >= -- 0.7 -- a relation -- it is --] -- containing -- being according to claim 10 -- a rigid film -- covering -- super- -- high temperature high pressure -- a sintered compact .

[Claim 12]A rigid film covering super-high-temperature-high-pressure sintered compact given in any 1 paragraph of claims 1-6 whose above-mentioned rigid films are the multilayers more than two-layer [of the above-mentioned Ti compound layer and the above-mentioned Ti-aluminum content compound layer].

[Claim 13]A rigid film covering super-high-temperature-high-pressure sintered compact given in any 1 paragraph of claims 10-12 which the above-mentioned rigid film becomes by inclination presentation in which aluminum elemental content in the above-mentioned Ti-aluminum content compound layer decreased toward the above-mentioned substrate side from the surface of this Ti-aluminum content compound layer.

[Claim 14]The above-mentioned rigid film which adjoins the above-mentioned substrate and is covered, A rigid film covering super-high-temperature-high-pressure sintered compact given in any 1 paragraph of claims 7-13 which at least one sort of rigid film strengthening substances chosen into this rigid film from metal of nickel, Co, W, Mo, aluminum, and Ti, these mutual alloys, and these intermetallic compounds contain.

[Claim 15]A rigid film covering super-high-temperature-high-pressure sintered compact in which a rigid film covering super-high-temperature-high-pressure sintered compact of a statement is used for any 1 paragraph of above-mentioned claims 1-14 as a cutting tool.

[Claim 16]The rigid film covering super-high-temperature-high-pressure sintered compact according to claim 15 in which, as for the above-mentioned cutting tool, film thickness of the above-mentioned tunic is decreasing toward a ridgeline part.

[Translation done.]

(19) 日本国特許庁 (J P)

(12) 公開特許公報 (A)

(11) 特許出願公開番号

特開2002-3284

(P2002-3284A)

(43) 公開日 平成14年1月9日(2002.1.9)

(51) Int.Cl. ⁷	識別記号	F I	テーム ⁷ (参考)
C 0 4 B 41/87		C 0 4 B 41/87	N 3 C 0 4 6
B 2 3 B 27/14		B 2 3 B 27/14	B 4 K 0 2 9
			A
B 2 3 P 15/28		B 2 3 P 15/28	A
C 0 4 B 41/89		C 0 4 B 41/89	J
審査請求 有 請求項の数16 O L (全 11 頁) 最終頁に続く			

(21) 出願番号 特願2000-178137(P2000-178137)

(22) 出願日 平成12年6月14日(2000.6.14)

(71) 出願人 006221144

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Fターム(参考) 3C04B FF02 FF10 FF13 FF16 FF25

FF35 FF38 FF39 FF40 FF42

FF47 FF49 FF53

4K029 A04 B41 B44 B45 B45

B45 B46 B46 B47 B47

B47 B47

(54) 【発明の名称】 硬質膜被覆超高温高压焼結体

(57) 【要約】 (修正有)

【課題】硬質膜と隣接する物質との密着性等が改善された切削工具等に用いられる硬質膜被覆焼結体の提供。

【解決手段】立方晶窒化硼素及び/又はダイヤモンドを含有する超高温高压焼結体となる基材の表面に被膜が被覆されており、該被膜はTi化合物層、ならびにTi-A1含有化合物層の中から選ばれた1種の単層または2種以上の多層でなる硬質膜を有しており、該硬質膜が立方晶結晶構造からなり、該硬質膜の(111)、(200)、(220)及び(311)の結晶面が表示される範囲をX線回折したときに、X線回折ピークの中で(200)結晶面が第1番目に高いピーク強度(「A」と表す)を示し、第2番目に高いピーク強度(「B」と表す)に対し、A/B≧8.5の関係を有し、かつ第3番目に高いピーク強度(「C」と表す)に対し、B/C≧2.0の関係を有する硬質膜被覆超高温高压焼結体。

1

【特許請求の範囲】

【請求項1】立方晶型窒素および/またはダイヤモンドを含有する超高温高圧焼結体である基材の表面に被膜が被覆されており、該被膜は、チタンの炭化物、窒化物、炭窒化物、炭酸化物、窒酸化物、炭窒酸化物であるTi化合物層、ならびにチタンとアルミニウムを含む複合窒化物、複合炭化物、複合炭酸化物、複合窒酸化物、複合炭酸化物、複合炭酸窒化物であるTi-Al含有化合物層の中から選ばれた1種の単層または2種以上の多層である硬質膜を有しており、該硬質膜が立方晶型窒素からなり、該硬質膜の表面から銅ターゲットを用いて、該硬質膜の(111)、(200)、(220)および(311)の結晶面が表示される範囲をX線回折したときに、X線回折ピークの中で(200)結晶面が第1番目に高いピーク強度(「A」と表す)を示し、第2番目に高いピーク強度(「B」と表す)に対する該第1番目に高いピーク強度の比が、5以上(A/B \geq 8.5)からなり、かつ第3番目に高いピーク強度(「C」と表す)に対する該第2番目に高いピーク強度(B/C)の比が、2.0以下(B/C \leq 2.0)である硬質膜被覆超高温高圧焼結体。

【請求項2】上記基材は、立方晶型窒素を40~98重量%と、残部がTiの炭化物、窒化物、炭窒化物、窒化物、Alの窒化物、炭化物、窒化物、Siの窒化物、炭化物、Mgの炭化物、Wの炭化物、およびこれらの相互固溶体、TiとAlとMgを含む複合窒化物、複合炭酸窒化物、ならびにAl、Ti、Co、Ni、Si、これらの相互合金、金属間化合物の中から選ばれた少なくとも1種の補強分散物質とを含有する請求項1に記載の硬質膜被覆超高温高圧焼結体。

【請求項3】上記基材は、該基材の表面粗さがJIS規格のRaによる平均表面粗さで0.1 μ m以下からなる請求項1または2に記載の硬質膜被覆超高温高圧焼結体。

【請求項4】上記被膜は、上記硬質膜と、該硬質膜に隣接して被覆された酸化アルミニウムの層を含んだ積層である請求項1~3のいずれか1項に記載の硬質膜被覆超高温高圧焼結体。

【請求項5】上記被膜は、該被膜の表面粗さがJIS規格のRaによる平均表面粗さで0.1 μ m以下からなる請求項1~4のいずれか1項に記載の硬質膜被覆超高温高圧焼結体。

【請求項6】上記硬質膜は、上記基材の表面に対し、垂直方向に柱状である柱状結晶が含まれている請求項1~5のいずれか1項に記載の硬質膜被覆超高温高圧焼結体。

【請求項7】上記硬質膜は、上記基材に隣接して被覆されている請求項1~6のいずれか1項に記載の硬質膜被覆超高温高圧焼結体。

【請求項8】上記基材に隣接して被覆される上記硬質膜

2

は、チタンの炭化物、窒化物、炭窒化物、炭酸化物、窒酸化物、炭酸窒化物の中の少なくとも1種のTi化合物層である請求項7に記載の硬質膜被覆超高温高圧焼結体。

【請求項9】上記Ti化合物層は、Ti(C_x, N_y, O_z)で表されるTi化合物層、[ただし、xは非金属元素中の炭素(C)元素の原子比、yは非金属元素中の窒素(N)元素の原子比、zは非金属元素中の酸素(O)元素の原子比、wは金属元素であるチタン(Ti)元素に対する非金属元素の原子比を表し、それぞれがx+y+z=1、0.5 \leq x \leq 0.1 \geq y \geq 0.5、0.5 \geq z \geq 0.1、0.5 \geq w \geq 0.7の範囲にある]を含有する請求項8に記載の硬質膜被覆超高温高圧焼結体。

【請求項10】上記基材に隣接して被覆される上記硬質膜は、チタンとアルミニウムを含む複合窒化物、複合炭化物、複合炭酸窒化物、複合窒酸化物、複合炭酸窒化物、複合炭酸窒化物の中の少なくとも1種のTi-Al含有化合物層である請求項7に記載の硬質膜被覆超高温高圧焼結体。

【請求項11】上記Ti-Al含有化合物層は、(Ti_a, Al_b)(C_x, N_y, O_z)で表されるTi-Al含有化合物層[ただし、aは金属元素中のTi(チタン)元素の原子比、bは金属元素中のAl(アルミニウム)元素の原子比、xは非金属元素中の炭素(C)元素の原子比、yは非金属元素中の窒素(N)元素の原子比、zは非金属元素中の酸素(O)元素の原子比、wは金属元素の合計に対する非金属元素の合計の原子比を表し、それぞれがa+b=1、0.8 \geq a \geq 0.4、x+y+z=1、0.5 \geq x \geq 0.1 \geq y \geq 0.5、0.5 \geq z \geq 0.1、0.5 \geq w \geq 0.7の範囲にある]を含有する請求項10に記載の硬質膜被覆超高温高圧焼結体。

【請求項12】上記硬質膜は、上記Ti化合物層と上記Ti-Al含有化合物層との2層以上の多層である請求項1~6のいずれか1項に記載の硬質膜被覆超高温高圧焼結体。

【請求項13】上記硬質膜は、上記Ti-Al含有化合物層中のAl元素含有量が該Ti-Al含有化合物層の表面から上記基材側に向かって減少した傾斜組成となる請求項10~12のいずれか1項に記載の硬質膜被覆超高温高圧焼結体。

【請求項14】上記基材に隣接して被覆される上記硬質膜は、該硬質膜中にNi、Co、W、Mo、Al、Tiの金属、これらの相互合金、これらの金属間化合物の中から選ばれた少なくとも1種の硬質膜強化物質が含有されている請求項7~13のいずれか1項に記載の硬質膜被覆超高温高圧焼結体。

【請求項15】上記請求項1~14のいずれか1項に記載の硬質膜被覆超高温高圧焼結体は、切削工具として用いられる硬質膜被覆超高温高圧焼結体。

【請求項16】上記切削工具は、上記被膜の膜厚が被

50

鏡面に向かって減少している請求項15に記載の硬質膜被覆超高温高压焼結体。

【発明の詳細な説明】

【0001】

【発明の属する技術分野】本発明は、立方晶型窒素および/またはダイヤモンドを含有する超高温高压焼結体の基材上にT1化合物層および/またはTi-A1含有化合物層の単層または多層でなる硬質膜を含む被覆が被覆された硬質膜被覆超高温高压焼結体に関するものである。

【0002】

【従来の技術】従来から超硬度物質であるダイヤモンドおよび/または立方晶型窒素の粉末と金属および/またはセラミックスの粉末との混合粉末を超高温高压装置により焼結した超高温高压焼結体が実用されている。この超高温高压焼結体を基材とし、この基材上に、化学蒸着法(以下、「CVD法」という)、物理蒸着法(以下、「PVD法」という)またはプラズマCVD法を利用して硬質膜を被覆した硬質膜被覆焼結体が提案されている。この硬質膜被覆焼結体の代表的なものに、特開昭59-8679号公報、特開昭61-183187号公報、特開平1-96083号公報、特開平1-96084号公報、および特開平7-24606号公報がある。

【0003】また、従来から超硬合金、サーメットの焼結合金またはセラミックス焼結体を基材とし、この基材上に、CVD法、PVD法またはプラズマCVD法を利用して硬質膜を被覆した被覆焼結部材が多様な形態で実用されてきている。これらの被覆焼結部材のうち、硬質膜の結晶構造に注目したものの代表的なものに、特開昭52-28478号公報、特開平8-209335号公報、特開平291353号公報、特開平9-295204号公報、特開平9-300105号公報、特開平9-300106号公報、特開平9-323204号公報、特開平9-323205号公報、特開平10-76407号公報、特開平10-76408号公報、特開平11-17622号公報、特開平11-131214号公報、特開平11-131215号公報、特開平11-131216号公報、および特開平11-131217号公報がある。

【0004】

【発明が解決しようとする課題】従来技術として挙げた引用文献のうち、特開昭59-8679号公報、特開昭61-183187号公報、特開平1-96083号公報、特開平1-96084号公報、および特開平7-24606号公報には、主として立方晶型窒素を含有した超高温高压焼結体を基材とし、この基材表面にT1の炭化物、窒化物、炭窒化物および酸化アルミニウムなどの硬質膜を単層または多層に被覆した硬質膜被覆焼結体が開示されている。これら5件の同公報に開示の硬質膜被覆焼結体は、硬質膜の膜質を主な特徴とする場合、単

層または多層でなる硬質膜の構成を主な特徴とする場合、焼結体の基材組成成分を主な特徴とする場合などがある。これら5件の公報に開示の硬質膜被覆焼結体は、一見、基材自体の優れた効果と硬質膜自体の優れた効果を融合させていると考えられるが、特に基材と硬質膜との適合性について配慮されていないことから、硬質膜の剥離により短寿命になるという問題がある。また、近年のようなエコロジー問題、資源問題に端を発して、切削油を使用しない切削加工用工具、被削材の材質変更などを含めた多様化に伴う最適切削工具、さらなる高速切削条件、高負荷切削条件、高効率切削条件などの市場の要求に達する切削工具などに対しては、同5件の公報に開示の硬質膜被覆焼結体は、硬質膜の剥離し易さ、または耐熱性、耐熱衝撃性の不足などにより短寿命になる傾向が高いという問題がある。

【0005】その他の引用文献として挙げた特開昭52-28478号公報、特開平8-209335号公報、特開平291353号公報、特開平9-295204号公報、特開平9-300105号公報、特開平9-300106号公報、特開平9-323204号公報、特開平9-323205号公報、特開平10-76407号公報、特開平10-76408号公報、特開平11-17622号公報、特開平11-131214号公報、特開平11-131215号公報、特開平11-131216号公報、および特開平11-131217号公報には、超硬合金、サーメットの焼結合金またはセラミックス焼結体を基材とし、この基材上に、周期律表4族の炭化物、窒化物、炭窒化物、ならびにタンタルとアルミニウムを含む複合窒化物、複合炭化物、複合炭窒化物、複合炭酸化物、複合炭酸炭化物、複合炭酸炭化物でなるTi-A1含有化合物の硬質膜が被覆された被覆焼結部材が開示されている。

【0006】これら15件の同公報に開示の被覆焼結部材は、主として基材表面の硬質膜を種々の形態に配向したことを特徴とするものである。これら15件の同公報の中には、硬質膜内の残留圧縮応力を考慮している場合、または硬質膜内の結晶配向を考慮している場合などがあり、その効果として硬質膜の粒界破壊の抑制、基材と硬質膜との密着性の向上、耐熱性性の向上、安定した切削加工、または長寿命の達成などが開示されている。しかしながら、これら15件の同公報に開示の被覆焼結部材は、硬質膜に存在する結晶の欠陥および歪みについて配慮されていないことから、基材と硬質膜との密着性および硬質膜に隣接する他の膜との密着性に満足できず、硬質膜自体の強度、耐摩耗性に満足するまでに至らず、寿命のパラッキが大きく、切削工具として実用したときに前述したような市場の要求に対して、主に硬質膜の剥離の容易さ、または耐熱性、耐熱衝撃性などの不足により短寿命になるという問題がある。

5

【0007】本発明は、上述のような問題点を解決したもので、具体的には、主として超高温高圧焼結体の基材と、この基材に隣接して被覆される硬質膜との結晶構造の適合性、硬質膜の結晶の欠陥、歪み、結晶構造および結晶配向を配慮することにより、基材と硬質膜との密着性を極端に高めて、硬質膜の特性のパラッキを抑制し、高剛性、高硬度性、耐摩耗性、耐酸化性、耐熱衝撃性、耐欠損性、耐溶着性のある硬質膜とし、切削工具としての使用領域を拡大し、被削材との耐溶着性を向上させた硬質膜とすることにより層長寿命を達成させた硬質膜被覆超高温高圧焼結体の提供を目的とするものである。

【0008】

【課題を解決するための手段】本発明者は、CVD法、PVD法およびプラズマPVD法に関する硬質膜の成膜についての研究、特にPVD法による硬質膜についての研究を長期に亘って行ってきた結果、立方晶型化離素および/またはダイヤモンドを含む超高温高圧焼結体である基材の表面にTi化合物層および/またはTi-A1含有化合物層である硬質膜を被覆させる場合に、最適な硬質膜構成があるという知見を得たものである。この知見を具体的に説明すると、硬質膜の成膜時におけるプラズマ密度の向上およびイオン化効率の向上を行い、さらに気相法エビタキシャル成長させる状態にすると、硬質膜内の歪みが均一に緩和されることが、硬質膜の結晶の欠陥が抑制されること、鉄酸化物の硬質膜が得られること、従来には見られない極端に最適な状態に配向された結晶の硬質膜となることから、硬質膜自体の強度、耐摩耗性、耐酸化性および耐熱性を向上させることが可能となり、硬質膜と基材との密着性の向上が顕著になるといふ第1の知見と、硬質膜の結晶の配向状態は、硬質膜の表面からX線回折したときに、硬質膜中の他の結晶面に対し(200)結晶面のピーク強度が極端に高くなることにより判断できるといふ第2の知見が主なるものである。これらの知見に基づいて、本発明を完成するに至ったのである。

【0009】本発明の硬質膜被覆超高温高圧焼結体は、立方晶型化離素および/またはダイヤモンドを含む超高温高圧焼結体である基材の表面に被膜が被覆されており、該被膜は、チタンの炭化物、窒化物、炭窒化物、炭酸化物、炭酸炭化物、炭酸炭酸炭化物であるTi-A1含有化合物層の中から選ばれた1種の単層または2種以上の多層の硬質膜を有しており、該基材に隣接して被覆される該硬質膜が立方晶結晶構造となり、該硬質膜の表面から銅ターゲットを用いて、該硬質膜の(111)、(200)、(220)および(311)の結晶面が表示される範囲をX線回折したときに、X線回折ピークの中で(200)

6

(0)結晶面が第1番目に高いピーク強度(「A」と表す)を示し、第2番目に高いピーク強度(「B」と表す)に対する該第1番目に高いピーク強度の比が8.5以上(A/B \geq 8.5)からなり、かつ第3番目に高いピーク強度(「C」と表す)に対する該第2番目に高いピーク強度(B)の比が2.0以下(B/C \leq 2.0)であることを特徴とするものである。

【0010】本発明の硬質膜被覆超高温高圧焼結体は、気相法エビタキシャル成長技術を応用して、Ti化合物層およびTi-A1含有化合物層の単層または多層である硬質膜における(200)結晶面の配向を強くし、硬質膜内の歪みを極力抑制することにより、硬質膜自体の強度、剛性を高めると共に、耐摩耗性も優れたようなシナージ効果を発現させたものである。この硬質膜の表面から銅ターゲットを用いてX線回折したときに、第2番目に高いピーク強度(B)に対する(200)結晶面のピーク強度(A)が8.5未満(A/B $<$ 8.5)で、かつ第3番目に高いピーク強度(C)に対する該第2番目に高いピーク強度(B)の比が2.0を超えて高くなる(B/C $>$ 2.0)場合には、(200)結晶面への配向性が弱く、膜内の欠陥および歪みが大きくなり、上述のシナージ効果が弱くなることから、上述のような結晶面のピーク高さ比と定めたものである。この結晶面のピーク強度比は、A/B \geq 9.0およびB/C \leq 1.5からなることが好しく、特にA/B \geq 10.0およびB/C \leq 1.5である場合には、より層の結晶配向性の促進および欠陥や歪みの抑制が図られて、基材との密着性を高めることになり、好ましいことである。

【0011】

【発明の実施の態様】本発明の硬質膜被覆超高温高圧焼結体における基材は、従来から実用または周知となっていた立方晶型化離素および/またはダイヤモンドを含む超高温高圧焼結体を用いることができる。具体的には、例えば立方晶型化離素の含有した超高温高圧焼結体の基材では、立方晶型化離素の含有量を20~98重量%と、残部が周期表の4a, 5a, 6a族の金属、Mn, Fe, Ni, Co, Si, Al, Mgの金属、これらの合金、これらの炭化物、窒化物、炭酸化物、硼化物、およびこれらの相互固溶体の中から選ばれた1種以上の補強分散物質とである立方晶型化離素含有焼結体を挙げることができる。また、例えばダイヤモンドの含有した超高温高圧焼結体の基材では、ダイヤモンドの含有量を70~99重量%と、残部が上述の補強分散物質とであるダイヤモンド含有焼結体を挙げることができる。さらに、例えば立方晶型化離素とダイヤモンドの混在した超高温高圧焼結体の基材では、立方晶型化離素の含有量を15~80重量%と、ダイヤモンドの含有量を15~80重量%と、残部が上述の補強分散物質とである焼結体を挙げることができる。

【0012】これらの基材のうち、立方晶型化離素を4

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$\geq x \geq 0$, $1 \geq y \geq 0$, $5 \cdot 0 \leq z \leq 0$, $1 \cdot 0 \leq w \leq 0$, 7 の関係にある」で表される Ti 化合物層となる場合には、上述の硬質膜の効果を容易に発揮させることから、好ましいことである。

【0020】また、基材に隣接する硬質膜は、単層または多層でなる Ti—Al 含有化合物層の場合がある。この Ti—Al 含有化合物層は、 (Ti_x, Al_y)

(Cr, N_y, O_z) 、 $[Ta, z]$ 、 a は金属元素中の Ti (チタン) 元素の原子比、 b は金属元素中の Al (アルミニウム) 元素の原子比、 x は非金属元素中の炭素

(C) 元素の原子比、 y は非金属元素中の窒素 (N) 元素の原子比、 z は非金属元素中の酸素 (O) 元素の原子比、 w は金属元素の合計に対する非金属元素の原子比を

表し、それぞれが $a+b=1$, $0 \cdot 8 \leq a \leq 0 \cdot 4$, $x+y+z=1$, $0 \cdot 5 \leq x \leq 0$, $1 \geq y \geq 0$, $5 \cdot 0$, $5 \leq z \leq 0$, $1 \cdot 0 \leq w \leq 0$, 7 の関係にある」で表

される Ti—Al 含有化合物層である場合には、基材と硬質膜と酸化アルミニウムの層との各界面における密着性および整合性に優れること、高温における耐磨耗性、耐酸化性に優れることから、好ましいことである。さら

に、硬質膜は、Ti 化合物層と Ti—Al 含有化合物層とでなる多層からなる場合もあり、この硬質膜の構成は、上述と同様の効果とともに、より広い温度領域にお

いて耐磨耗性、耐酸化性を発揮させることから、好ましいことである。

【0021】これらの基材に隣接する硬質膜を含めた全ての硬質膜中において、Ti—Al 含有化合物層が存在している場合には、Ti—Al 含有化合物層中の Al 元素含有量が Ti—Al 含有化合物層の表面側から基材側

に向かって減少していること、いわゆる傾斜組成の硬質膜にすると基材と硬質膜との密着性が優れること、硬質膜自身の強度、靱性に優れて、欠陥、歪みおよび残留応力が減少すること、硬質膜表面の耐酸化性、耐磨耗性および耐腐食性が優れることから、好ましいことである。

このときの Al 元素の減少は、階段状、ノコギリの形状にミクロ的に増減があるとしてもマクロ的には段階的に減少する場合、放物線状、直線状に連続的に減少している場合でもよいものである。

【0022】これらの Ti 化合物層および/または Ti—Al 含有化合物層でなる硬質膜、特に基材に隣接する硬質膜は、該硬質膜中に周期律表の 4a, 5a, 6a 族金属、鉄族金属、Al, Si, Mn, Mg これらの合金または金属間化合物の中の少なくとも 1 種の硬質膜強化物質が微量含有されている場合がある。これらの硬質膜強化物質のうち、Ni, Co, W, Mo, Al, Ti の金属、これらの相互合金、これらの金属間化合物の中から選ばれた少なくとも 1 種である場合には、欠陥、歪みが緩和されて前述の硬質膜の効果がより一層向上し、顕著となることから、好ましいことである。特に、基材に含有している元素、具体的に、例えば前述の立方晶

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化硼素含有結晶体である基材の場合には、補強分散物質を構成する元素からなると、前述の硬質膜の効果とともに、基材と硬質膜との密着性の効果もより一層向上することから、好ましいことである。

【0023】これらの硬質膜強化物質の含有量としては、具体的には、硬質膜と硬質膜強化物質との合計に対して、3 体積%以下、好ましくは 1 体積%以下含有していること、密着硬質膜の表面からの垂直方向および水平方向の両方からの耐圧強度、耐圧強度に優れるとともに、耐磨耗性に優れるという相乗効果が発揮されること

から、好ましいことである。

【0024】また、硬質膜自体の構造としては、基材表面に対し垂直方向に柱状に成長した柱状結晶が含まれている場合には、密着硬質膜の表面からの耐圧強度が向上し、耐剥離性、耐微小チップング性に優れることから、好ましいことである。この柱状結晶を含む硬質膜は、具体的には、硬質膜全体が柱状結晶の層である場合、柱状結晶と柱状結晶との混在した層である場合、粒

状結晶の層と柱状結晶の層との積層である場合、またはこれらの粒状結晶と柱状結晶のそれぞれの中に前述した硬質膜強化物質が微量含有されている場合を例示することができる。

【0025】以上のような各種の態様でなる本発明の硬質膜被覆超高温高圧燃焼体は、各種の用途に実用できるものであり、具体的には、例えば鍛造工具、フライス工具、ドリル、エンドミルに代表される切削工具、ダイスなどの型工具からスリッターなどの削刃刀、切断刃などの耐摩耗用工具として実用できるものである。これらのうち、本発明の硬質膜被覆超高温高圧燃焼体は、ミクロ的に温度、摩擦、熱衝撃および圧縮衝撃などが最も過酷な条件となる切削工具、特にドリル、エンドミルなどの回転切削工具、スローウエイチップなどの切削工具として使用する場合には、基材と硬質膜の特性を最適に発揮させる得ることから、好ましいことである。この硬質膜被覆超高温高圧燃焼体は、切削工具として使用する場合には、前述した表面における面積度の問題の他に、刃に

切れ、チップングなどに関連する切刃の問題がある。この切刃の問題は、例えば面取りおよび/または R 形状などのホーニング形状により解決することと好ましく、特に被膜厚さが切刃稜線部に向かって減少していること、被膜の耐剥離性、切刃の微小チップング性に優れることから好ましいことである。

【0026】また、被膜を構成する各層の膜厚さは、用途、形状および被膜の構成により、選択することが好ましく、最も過酷な切削工具などに使用する場合には、被膜の総膜厚さを 1—20 μm にすることが好ましいことである。また、耐磨耗工具などに使用する場合には、さらに被膜の膜厚さを厚くすることも可能であるが、被覆工程が長時間となることなどから、上述の総膜厚が程度

にておくことが好ましいことである。以上に詳述して

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きた硬質膜を初め、基材に含有する補強分散物質は、化学量論組成でなる場合、または非化学量論組成でなる場合でもよく、実質的には非化学量論組成からなっている場合が多いものである。

【0027】この本発明の硬質膜被覆超高温高压焼結体は、従来から市販されている立方晶型化硼素系統結体、ダイヤモンド系統結体に代表される超高温高压焼結体または前述した立方晶型化硼素含有の超高温高压焼結体を基材とし、この基材の表面を、必要に応じて研磨し、超音波洗浄、有機溶剤洗浄などを行った後に、従来から行われているPVD法、CVD法またはプラズマCVD法により基材上に被覆膜を被覆して作製することができる。特に、基材表面に隣接して被覆される硬質膜は、以下のPVD法で作製すると、プラズマ密度の向上とイオン化効率の向上が可能となること、硬質膜自体の気相エピタキシャル結晶成長および結晶配向が容易となること、硬質膜の特性および密着性がより優れることから、好ましいことである。

【0028】基材表面に隣接して被覆される硬質膜を被覆するための方法として、重要な特徴について具体的に詳述すると、基材の表面は、従来から行われているブラスト処理、ショットピーニング処理、研磨処理、バレル処理の中の少なくとも1種の機械的処理と、酸性もしくはアルカリ性の電解液による電解エッチング、酸溶液、アルカリ溶液による表面腐食、または水、有機溶液による洗浄の中の少なくとも1種の化学的処理と、この機械的処理と化学的処理を同時または別々に行う処理方法とから選択される処理を行うと、基材表面の欠陥を除去できること、硬質膜の密着性を高め得ること、膜内歪みを抑制できること、膜内の欠陥を抑制できることから、好ましいことである。また、基材は、このような機械的処理および/または化学的処理と、低温による熱処理を付加して、上述の効果を高めることも好ましいことである。

【0029】硬質膜の被覆方法は、スパッター法やイオンプレーティング法に代表されるPVD法により行うことが好ましく、これらのうち、マグネトロンスパッター法またはアークプラズマイオンプレーティング法により行うと、硬質膜の調整が容易であることから、特に好ましいことである。具体的には、例えばイオンプレーティング装置の反応容器内に基材を配置し、基材表面をボンバード処理する場合に、金属元素および/または非金属元素のイオンによるボンバード処理、もしくは金属元素イオンと非金属元素イオンの両方によるボンバード処理を施すと、上述の効果を高めることになり、好ましいことである。

【0030】さらに具体的な硬質膜の被覆方法は、反応容器の構造、プラズマの調整など装置自体の影響を重要視する必要がある、例えば高電圧の電源（場合によってはパルス状高電圧と高周波を付加）でイオンの加速とブ

ラズマを発生させる装置、磁界によるプラズマの調整可能な装置を使用すること、その他、反応容器内の雰囲気圧力、温度、アーク放電電流、電圧、基材バイアス電圧、試料の配置などについて配慮する必要がある、これらのうち、従来の条件に対し、特にアーク放電電圧を高くすること、基材バイアス電圧を高くすること、従来から行われている気相エピタキシャル結晶成長法を取り入れること、試料の回転および上下動などが重要な要件となる。

【0031】

【発明の実施の形態】

【実施試験1】以上に詳述してきた本発明の実施形態について、さらに具体的な代表例として実施試験により説明する。まず、従来の配合、混合、成形、焼結の各工程を経て作製されたISO規格によるSNGN12040B形状相当の超硬合金を台金とし、この超硬合金台金の刃先となるコーナ部に表1に示した組成成分でなる立方晶型化硼素含有の超高温高压焼結体の基材を接合し、複合焼結体を得た。この複合焼結体は、超硬合金台金と表1に示した立方晶型化硼素含有組成成分を圧力5.5GPa、温度1773Kの超高温高压焼結により、直接接合したものである。また、複合焼結体は、超硬合金台金と超高温高压焼結体を銀糊1付けにより接合した場合でもよい。これらの複合焼結体の上面と外面を270#のダイヤモンド砥石で研削加工を施し、刃先部に400#ダイヤモンド砥石により2°×0.10mmのホーニング加工を施し、さらに表面を湿式ブラスト処理、洗浄処理および乾燥処理を行った後、アークイオンプレーティング装置により硬質膜を被覆した。

【0032】処理方法は、反応容器内の各複合焼結体表面（特に基材表面）をボンバード処理した後、硬質膜を被覆した。ボンバード処理は、反応容器内の雰囲気圧を真空、基材の温度を823〜873K、アーク電流を60〜80A、基材のバイアス電圧を-400〜700Vとし、Ar-N₂ガスボンバードにより行った。硬質膜の被覆は、反応容器内のガス流量を150〜450SCCM、蒸発源をTi1金属（Ti1化合物層用）またはTi1-A1合金（Ti1-A1含有化合物層用）、アーク電圧を150〜350V、アーク電流を150〜250A、複合焼結体の基材温度を773〜923K、複合焼結体の基材バイアス電圧を-100〜200Vにより行い、表2に示した本発明品1〜10を得た。

【0033】このときの硬質膜被覆時の反応容器内雰囲気は、Ti1層および（Ti1, A1）層の場合がN₂ガス組成、Ti1（C, N）層の場合がN₂-C₂H₄ガス組成、Ti1（C, N, O）層の場合がN₂-CO-CO₂ガス組成、Ti1（C, N, O）層の場合がN₂-C₂H₄-COガス組成で行い、本発明品4の蒸発源には、Ti1元素の多い合金からA1元素の多い合金に切り替えて行い、表2に示した硬質膜

が被覆された本発明品1~10を得た。

【0034】比較として、市販されている立方晶窒化硼素含有の超高温高圧焼結体を、超硬合金に銀くっ付けして得た同形状の複合焼結体の表面にそれぞれ表3に示した硬質膜を被覆して比較品1~5を得た。複合焼結体の表面粗さは、上述の本発明品1~10に使用の複合焼結体の表面が $Ra=0.01\sim0.005\mu m$ に対し、比較品1~5に使用の複合焼結体の表面が $Ra=0.1\sim0.05\mu m$ であった。比較品1~5における複合焼結体の表面処理は、上述した本発明品の表面処理のうち、湿式プラスト処理を除いて、その他はほぼ同様に処理した。また、同比較品1~5におけるボンパード処理は、Arガスに行い、硬質膜の被覆は、上述した本発明品の硬質膜の処理条件のうち、アーク電圧を10~50V、アーク電流を150~200A、基材バイアス電圧を $-80\sim-200V$ とした以外は、ほぼ同様に処理した。

【0035】こうして得た本発明品1~10および比較品1~5のそれぞれについて、X線回折装置により、Cu α ターゲットを用いて、硬質膜表面から回折角度 $2\theta=30\sim80$ 度の範囲を回折し、硬質膜の(111)結晶面、(200)結晶面、(220)結晶面、(311)結晶面の各ピーク強度を測定した。ピーク強度の測定は、横軸が回折角(2θ)度で、縦軸がピーク強度を表すX線回折パターンのうち、それぞれ第1番目~第3番目までの強度の高いピークの高さをmm単位で測定し、その結果を表4および5に示した。表4の本発明品1~10における第1番目に高いピークは、(200)結晶面であり、第2番目および第3番目に高いピークは、(111)結晶面、(220)結晶面、(311)結晶面であり、(111)結晶面および(311)結晶面を測定した。表5の比較品1~5は、同様*

材料番号	超高温高圧焼結体の組成成分(配合時)	体積%
基材1	98CBN-1Al-1TiN	
基材2	95CBN-1Al-2Al ₂ O ₃ -2TiN	
基材3	90CBN-2Al-2B ₂ O ₃ -2Al ₂ O ₃ -2TiN	
基材4	80CBN-2Al-10Al ₂ O ₃ -5TiN-3Ti(C,N)	
基材5	70CBN-2Al-2B ₂ O ₃ -2TiN-2Ti(C,N)-5TiN	
基材6	60CBN-10Al-25Al ₂ O ₃ -5Ti(C,N)	
基材7	40CBN-10Al-35Al ₂ O ₃ -5(W,Ti)C-10TiN	
基材8	25CBN-28Al ₂ O ₃ -10WC-15Ti(C,N)-10Al ₂ O ₃ -2Co-2Mg	

【0039】
【表2】

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*に(200)結晶面、(111)結晶面および(311)結晶面を測定した。このときの発明品1~10の硬質膜は、立方晶結晶構造からなっていることを確認した。

【0036】これらの本発明品1~10および比較品1~5について、走査型電子顕微鏡、金属顕微鏡、EDS装置、ビッカース硬さ試験機および引張り硬さ試験機に相当するスクラッチ試験機を用いて、主として硬質膜の状態を調査した。これらの調査結果のうち、硬質膜の膜厚さは、表2および3に示した。硬質膜の耐削離性として測定したスクラッチ強度は、それぞれの結果を表6に示した。なお、本発明品1~10の硬質膜のうち、酸素の含有した硬質膜は、その硬質膜中の酸素含有量が非金属元素全体に対し、0.2原子比であった。(Ti, Al)Nの硬質膜層は、ほぼTi:Al=1:1であり、このうち本発明品4が基材側から膜表面に向かってAl元素の漸増した傾斜組成の(Ti, Al)N硬質膜層であった。また、本発明品5、10におけるTi(C, N)の硬質膜層は、柱状結晶からなっていた。【0037】次いで、本発明品1~10および比較品1~5を用いて、以下の切削条件により乾式連続切削試験を行った。切削条件は、被削材がPCD70、切削速度が500m/min、送り0.1mm/rev、切り込みが0.3mm、工具形状がSNGN120408、により行った。切削試験の結果は、切削のチッピング、被覆膜の剥離したとき、平均逃げ面摩耗量が0.2mmに達したときを工具寿命とし、そのときのそれぞれの切削時間を求めて、最短寿命の試料を1とし、最短寿命の試料に対する寿命比として、表6に併記した。

【0038】
【表1】

材料番号	材料番号	硬質膜の膜厚さ(nm)と材質
本発明品	基材1	5TiN
1	基材2	5CBN
2	基材3	5Ti(C,N)-4TiN
3	基材4	5TiN-5TiN
4	基材5	5TiN-4Ti(C,N)-5TiN-1TiN
5	基材6	5Ti(C,N)-4TiN
6	基材7	5TiN-4Ti(C,N)-1TiN
7	基材8	5TiN-4TiN-1TiN
8	基材9	5TiN-5TiN-1TiN
9	基材10	5TiN-5TiN-1TiN
10	基材11	5TiN-5TiN-1TiN

【表3】

試料番号	被覆の膜厚さ(μm)と材質
比較品1	STiN
比較品2	STiN/ADN
比較品3	STiN(C,N)-4(Ti,ADN)
比較品4	STiN-STiN(N,O)
比較品5	STiN-STiN(C,N)

* 【0041】

【表4】

※						
試料 番号	硬質膜の各結晶面強度			硬質膜の結晶面強度比		
	第1番目(A)	第2番目(B)	第3番目(C)	A/B	B/C	
本 発 明 品	1	70.0	4.5	4.0	10.5	1.1
	2	53.0	4.0	3.5	13.5	1.1
	3	48.5	4.5	4.0	10.8	1.1
	4	45.5	4.0	3.5	11.4	1.1
	5	75.0	5.0	4.0	15.0	1.3
	6	63.5	7.0	5.0	9.1	1.4
	7	87.0	7.0	6.0	9.6	1.2
	8	46.0	4.0	3.5	11.5	1.1
	9	45.0	3.0	3.0	15.0	1.0
	10	47.5	2.0	2.0	15.8	1.5

【0042】

※ ※ 【表5】

試料番号	被覆の各結晶面強度			被覆の結晶面強度比	
	(200)面(A)	(111)面(B)	(311)面(C)	A/B	B/C
1	89.0	21.0	15.0	3.3	1.4
2	58.0	13.0	2.0	4.5	6.5
3	80.0	0-6.0	2-29.0	2.8	3.5
4	59.0	53.0	5.0	0.6	10.5
5	15.0	85.0	6.0	0.2	10.5

【0043】

【表6】

試料番号	スクラッチ靱性(N)	切削試験での寿命比
本発明品	1	140
	2	130
	3	130
	4	140
	5	160
	6	140
	7	160
	8	140
	9	150
	10	140
比較品	1	80
	2	60
	3	50
	4	60
	5	80

★2, 3, 4, 10および表3に示した比較品1~5を用いて、それぞれの硬質膜表面に、さらにその他の膜として、従来からの方法によりAl₂O₃およびTiNの膜を被覆し、それぞれ表7に示した本発明品11~15および表8に示した比較品6~10を得た。こうして得た本発明品11~15および比較品6~10について、実施試験1と同様に硬質膜とその他の膜を調査し、被覆表面からのスクラッチ強度を求めて、その結果を表9に示した。また、本発明品11~15および比較品6~10について、実施試験1の切削条件と同様にして切削試験を行い、比較品1に対するそれぞれの寿命比を求めて、表9に併記した。

【0045】

【表7】

【0044】

【実施試験2】実施試験1の表2に示した本発明品1, ★

試料番号	被覆の膜厚さ(μm)と材質	
本発明品	基材番号	その他の膜
11	基材1	STiN
12	基材2	STiN/ADN
13	基材3	STiN(C,N)-4(Ti,ADN)
14	基材4	STiN-STiN/ADN
15	基材5	STiN-STiN(C,N)-TiN

【0046】

【表8】

☆ ☆

試料番号	被覆の膜厚さ(μm)と材質	
	硬質膜	その他の膜
比較品6	STiN	2Al ₂ O ₃ -TiN
比較品7	STiN/ADN	2Al ₂ O ₃ -TiN
比較品8	STiN(C,N)-4(Ti,ADN)	2Al ₂ O ₃ -TiN
比較品9	STiN-STiN(N,O)	2Al ₂ O ₃ -TiN
比較品10	STiN-STiN(C,N)	2Al ₂ O ₃ -TiN

【0047】

【表9】

試料番号	スクラッチ荷重(N)	切削試験での寿命比
本発明品 11	180	4.8
12	160	6.4
13	170	7.5
14	160	6.7
15	180	5.0
比較品 6	100	1.6
7	110	1.8
8	105	1.9
9	99	1.7
10	110	1.6

【0048】

【実施試験3】実施試験1の本発明品に使用した複合焼結体のうち、基材を表10に示した組成成分とした以外は、ほぼ同様にして本発明品16~20用の複合焼結体を得た。これらの複合焼結体の表面に、実施試験1および2と同様にして硬質膜、その他の膜を被覆し、表11に示した本発明品16~20を得た。これらの本発明品16~20について、実施試験1と同様に、硬質膜表面におけるX線回折による結晶面ピーク高さを求めて、その結果を表12に示した。また、本発明品16~20について、実施試験1および2とはほぼ同様にして、硬質膜または被膜表面からのスクラッチ強度を求めて、その*

*結果を表13に示した。次に、本発明品16~20と実施試験1における比較品1を用いて、被削材がA1-Si合金、切削速度が300m/min、送り量が0.1mm/rev、切り込みが0.2mm、工具形状がSNG N120408、の切削条件により乾式切削試験を行い、比較品1に対するそれぞれの寿命比を求めて、その結果を表13に併記した。このときの本発明品18および19は、被膜の膜厚さが被膜部に向かって減少するように、ダイヤモンド粉末とブラシによるブラシホーニング処理を行ったものである。また、本発明品16~20の硬質膜中には、極微量のCおよび/またはNが含まれている。

【0049】

【表10】

試料番号	焼結体の組成成分(配合時)	体積%
基材9	86DIA-20C	
基材10	86DIA-20C-3N	
基材11	80CBN-90DIA-2A1-20C-1N-5TiN	
基材12	80CBN-90DIA-2A1-40C-2N-5TiN	
基材13	45CBN-45DIA-2A1-2B-20C-2N-2Mg	

【0050】

【表11】

試料番号		被膜の膜厚さ(μm)と材質	
本発明品	基材番号	硬質膜	その他の膜
16	基材9	5TiN	なし
17	基材10	5(Ti,Al)N	なし
18	基材11	2Ti(C,N)-4(Ti,Al)N	なし
19	基材12	2TiN-1TiN(O)	3Al ₂ O ₃ -1TiN
20	基材13	2TiN-4Ti(C,N)-1TiN(O)	8Al ₂ O ₃ -1TiN

【0051】

※ ※ 【表12】

試料番号	硬質膜の各結晶面強度			硬質膜の結晶面強度比	
	第1番目(A)	第2番目(B)	第3番目(C)	A/B	B/C
本発明品 16	68.0	4.0	3.5	17.0	1.1
17	65.0	3.0	3.0	18.3	1.0
18	51.5	3.0	2.6	17.1	1.2
19	65.0	3.5	3.0	11.8	1.1
20	57.0	4.5	4.0	12.7	1.1

【0052】

【表13】

試料番号	スクラッチ荷重(N)	切削試験での寿命比
本発明品 16	170	2.0
17	160	3.5
18	180	5.5
19	150	6.0
20	170	4.7

【0053】

【発明の効果】本発明の硬質膜被覆超高温高圧焼結体は、基材と硬質膜との結晶構造による配座と、製法による配座により、気相法エピタキシャルに近似した結晶成長と結晶配向による硬質膜が被覆されていること、硬質膜自体の歪み、欠陥が抑制されていること、微細結晶の★

★硬質膜であること、場合によっては柱状結晶および/または微量の金属などの硬質膜強化物質が含まれた硬質膜であることから、従来の硬質膜被覆焼結体または本発明から外れた硬質膜被覆焼結体に対比して、基材と硬質膜および硬質膜と他の膜などの密着性および耐剥離性が非常に優れていること、複合硬質膜自体の高剛性、高強度、耐熱性、耐熱衝撃性、耐酸化性および耐摩耗性が優れていること、その結果として例えば切削工具として使用した場合に、切削工具として重要視される高剛性、耐摩耗性、耐熱衝撃性、耐欠損性、耐酸化性および耐溶着性が顕著に向上し、長寿命化が達成されること、切削加工における高効率化が達成されることが、パツキが小さく安定しているという顕著な効果がある。

(11)

特開2002-3284

フロントページの続き

(51)Int.Cl.⁷

C23C 14/06

識別記号

F I

C23C 14/06

テーマド(参考)

P